NTT AT

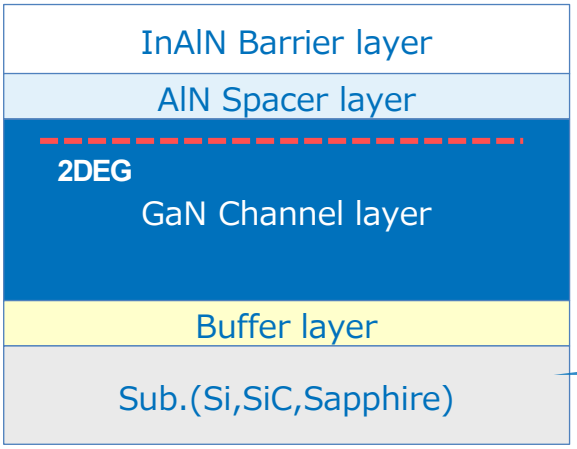
EPIWAFERS

Semi Conductor Devices

InAlN / GaN HEMT

For next generation high frequency and high output power devices

■ Typical Structure

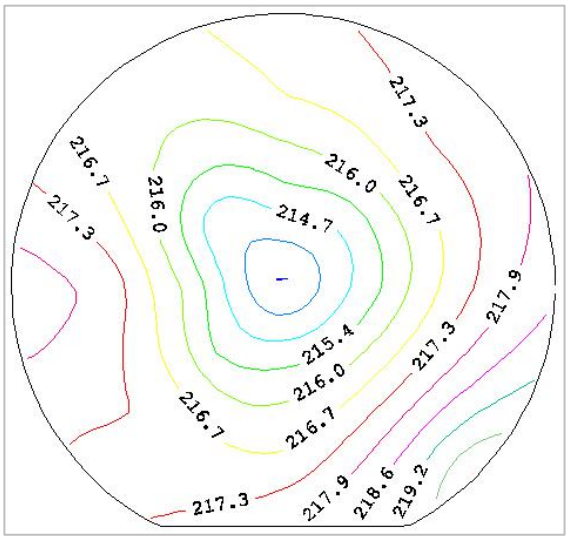


Si: up to 8 inch

SiC: up to 4 inch

Sapphire: up to 3 inch

■ Sheet resistivity distribution on 6 inch InAlN/GaN HEMT and hall effect



Ave.: 216 ohm/sq. (Var.: 3.6%)

Hall

Rs [ohm/sq.]	219
μ[cm²/Vs]	1300
Ns[cm⁻²]	2.20e13

*Some of the specifications may change without prior notice.

For Further Inquiry https://keytech.ntt-at.com/en/epi/prd_1002.html

NTT ADVANCED TECHNOLOGY CORPORATION